



#### 200V P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C	
-200V	28Ω @ V <sub>GS</sub> = 10V	-122mA	

#### **Description**

This new generation trench MOSFET features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

## **Applications**

 Active Clamping of Primary Side MOSFETs in 48 Volt DC-DC Converters

### **Features and Benefits**

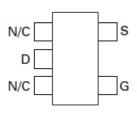
- High Voltage
- Low On-Resistance
- Fast Switching Speed
- Low Gate Drive
- Low Threshold
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

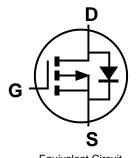
- Case: SOT25
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 0.016 grams (Approximate)







Pin Out - Top



Equivalent Circuit

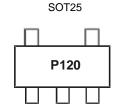
### Ordering Information (Note 4)

ĺ	Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	ZXMP2120E5TA	P120	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



P120 = Product Type Marking Code



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-200	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (V <sub>GS</sub> = 10V; T <sub>A</sub> = +25°C) (Note 5)	I <sub>D</sub>	-122	mA
Pulsed Drain Current (Note 6)	I <sub>DM</sub>	-0.7	A
Pulsed Source Current (Body Diode) (Note 6)	I <sub>SM</sub>	-0.7	A

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at $T_A$ = +25°C (Note 5) Linear Derating Factor	P <sub>D</sub>	0.75 6	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	167	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

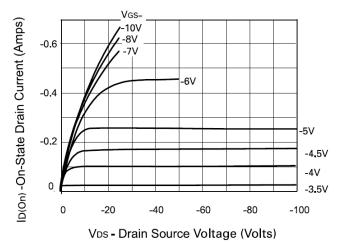
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS						•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-200	-	-	V	$V_{GS} = 0V$ , $I_D = -1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	-10 -100	μΑ	$V_{DS} = -200V, V_{GS} = 0V$ $V_{DS} = -160V, V_{GS} = 0V, T = +125$ °C	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	20	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.5	-	-3.5	V	$V_{DS} = V_{GS}$ , $I_D = -1mA$	
Static Drain-Source On-Resistance (Note 7)	R <sub>DS(ON)</sub>	-	-	28	Ω	$V_{GS} = -10V, I_D = -150mA$	
Forward Transconductance (Notes 7 & 8)	g <sub>fs</sub>	50	-	-	mS	$V_{DS} = -25V, I_{D} = -150mA$	
On-State Drain Current (Note 7)	I <sub>D(ON)</sub>	-300	-	-	mA	V <sub>DS</sub> = -25V, V <sub>GS</sub> = -10V	
DYNAMIC CHARACTERISTICS							
Input Capacitance (Note 8)	C <sub>iss</sub>	-	-	100	pF	$V_{DS} = -25V, V_{GS} = 0V,$	
Output Capacitance (Note 8)	Coss	-	-	25	pF		
Reverse Transfer Capacitance (Note 8)	C <sub>rss</sub>	-	-	7	pF	f = 1.0MHz	
Turn-On Delay Time (Notes 8 & 9)	t <sub>D(ON)</sub>	-	-	7	ns		
Turn-On Rise Time (Notes 8 & 9)	t <sub>R</sub>	-	-	15	ns	), osv. i 450 A	
Turn-Off Delay Time (Notes 8 & 9)	t <sub>D(OFF)</sub>	-	-	12	ns	$V_{DD} = -25V, I_{D} = -150mA$	
Turn-Off Fall Time (Notes 8 & 9)	t <sub>F</sub>	-	-	15	ns	1	

- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
  6. Repetitive rating pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.
  7. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

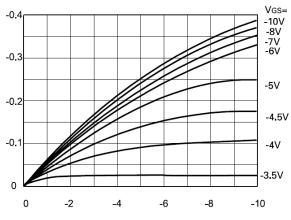
- 8. Sample test.
- Switching characteristics are independent of operating junction temperature.





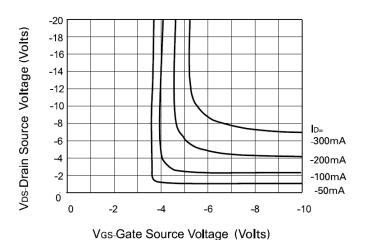




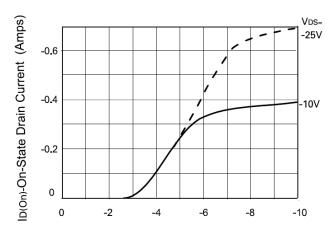


V<sub>DS</sub> - Drain Source Voltage (Volts)

## **Output Characteristics**

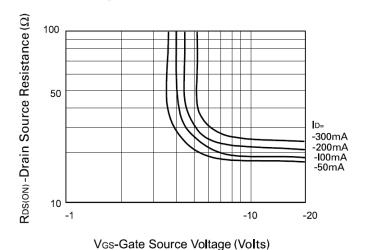


**Saturation Characteristics** 

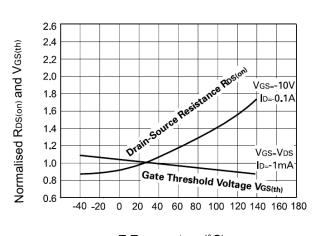


Vgs-Gate Source Voltage (Volts)

### **Voltage Saturation Characteristics**



**Transfer Characteristics** 

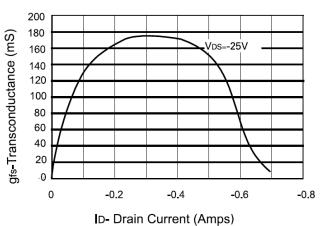


T-Temperature (°C)

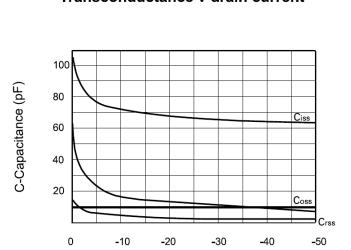
#### On-resistance vs gate-source voltage

#### Normalised RDS(on) and VGS(th) vs Temperature





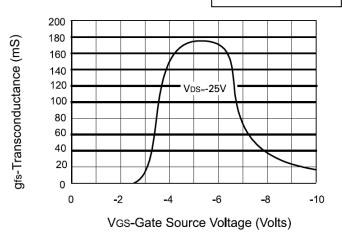
Transconductance v drain current



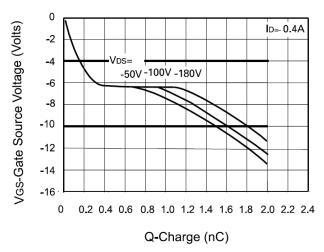
Capacitance v drain-source voltage

VDS-Drain Source Voltage (Volts)

## **ZXMP2120E5**



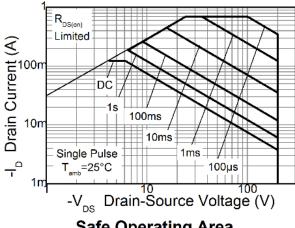
### Transconductance v gate-source voltage

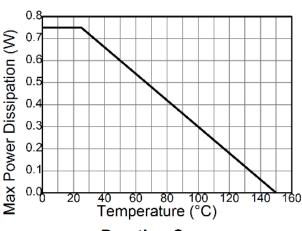


Gate charge v gate-source voltage

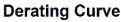


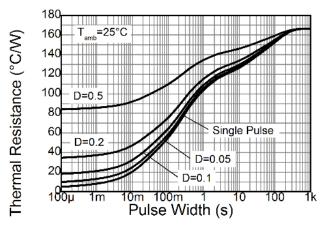
## **Thermal Characteristics**

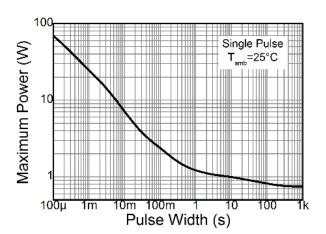












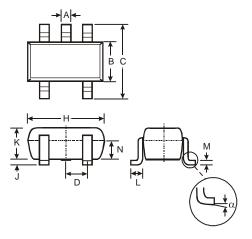
**Transient Thermal Impedance** 

**Pulse Power Dissipation** 



# **Package Outline Dimensions**

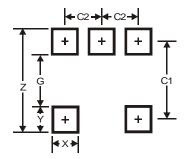
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT25				
Dim	Min	Max	Тур		
Α	0.35	0.50	0.38		
В	1.50	1.70	1.60		
С	2.70	3.00	2.80		
D	-	-	0.95		
Н	2.90	3.10	3.00		
J	0.013	0.10	0.05		
K	1.00	1.30	1.10		
L	0.35	0.55	0.40		
М	0.10	0.20	0.15		
Ν	0.70	0.80	0.75		
α	0°	8°	-		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	SOT25	
Z	3.20	
G	1.60	
Х	0.55	
Y	0.80	
C1	2.40	
C2	0.95	



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